

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07442 DT-33~13

SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SC1195

REGULATOR APPLICATIONS.

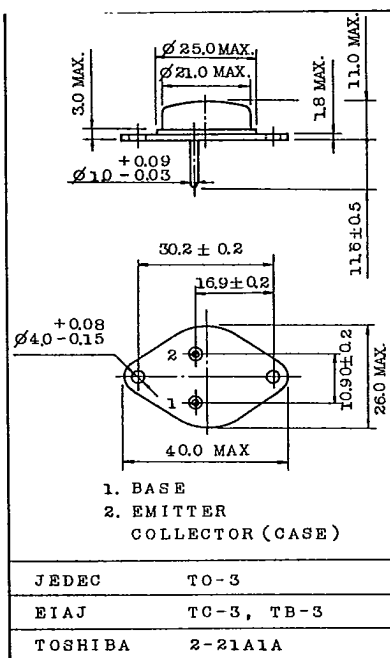
HIGH VOLTAGE SWITCHING APPLICATIONS.

FEATURES:

- High Voltage : $V_{CE0}=200V$
- Large Collector Current : $I_C=2.5A$
- Wide Safe Operating Area.

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	200	V
Collector-Emitter Voltage	V_{CEO}	200	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	2.5	A
Emitter Current	I_E	-2.5	A
Collector Power Dissipation ($T_c=25^\circ C$)	P_C	100	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-65 ~ 150	$^\circ C$



Mounting kit No. AC73
Weight : 12.0g

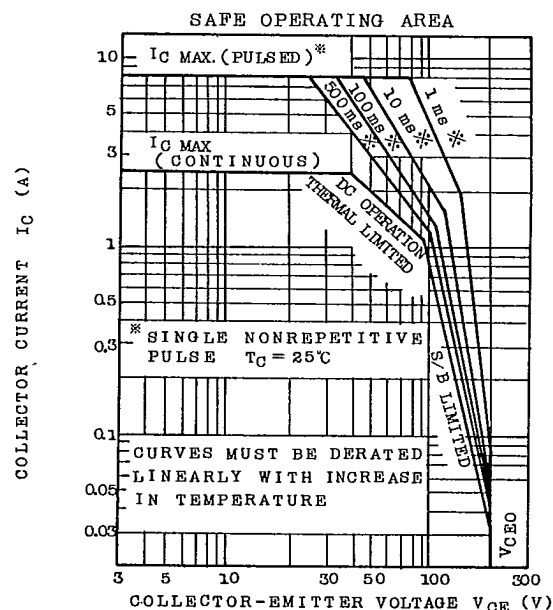
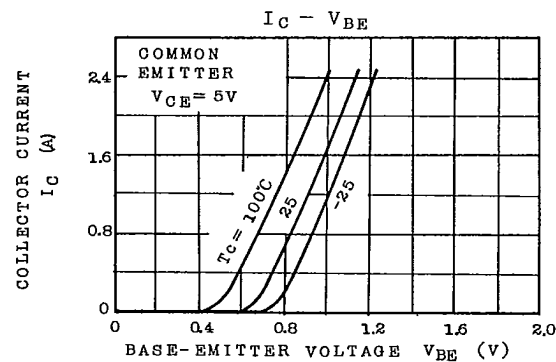
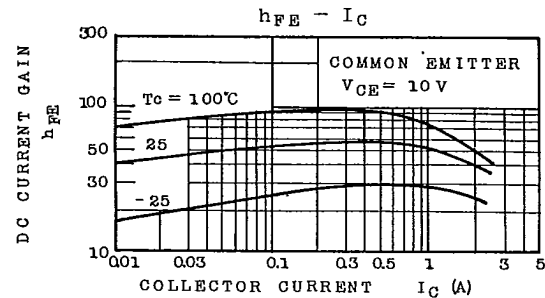
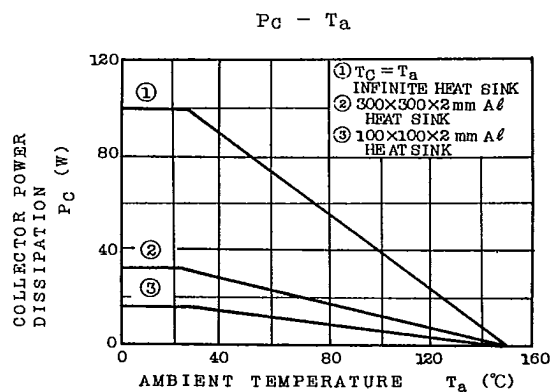
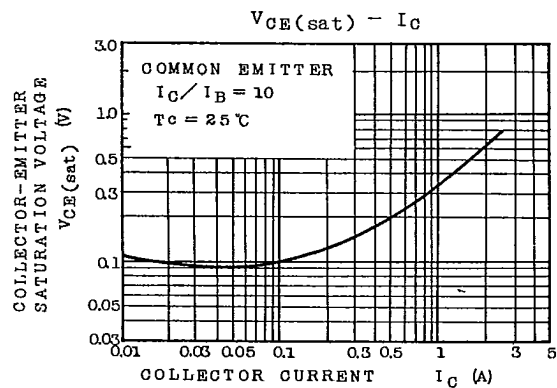
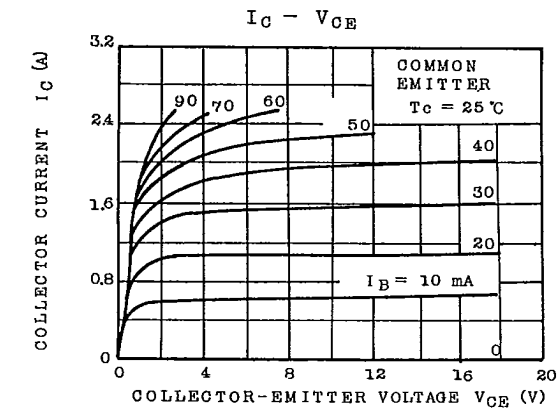
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=200V, I_E=0$	-	-	10	μA
	I_{CEO}	$V_{CE}=200V, I_B=0$	-	-	0.1	mA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	1.0	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	200	-	-	V
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=1A$	30	50	150	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1A, I_B=0.1A$	-	-	1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=1A, I_B=0.1A$	-	-	1.5	V

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